

ACTS125MS

Radiation Hardened Quad Buffer, Three-State

January 1996

Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96715 and Intersil' QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose>300K RAD (Si)
- Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/Bit/Day (Typ)
- SEU LET Threshold>100 MEV-cm²/mg
- Dose Rate Survivability>10¹² RAD (Si)/s, 20ns Pulse
- Latch-Up Free Under Any Conditions
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- Input Logic Levels
 - VIL = 0.8V Max
 - VIH = VCC/2 Min
- Input Current ≤ 1μA at VOL, VOH
- Fast Propagation Delay 17ns (Max), 11ns (Typ)

Description

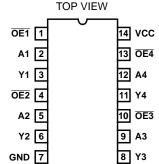
The Intersil ACTS125MS is a Radiation Hardened Quad Buffer with Three-State outputs. Each output has it's own enable input, which when "HIGH" puts the output in a high impedance state.

The ACTS125MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of radiation hardened, high-speed, CMOS/SOS Logic Family.

The ACTS125MS is supplied in a 14 lead Ceramic flatpack (K suffix) or a Ceramic Dual-In-Line Package (D suffix).

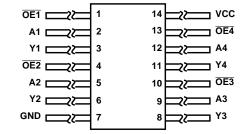
Pinouts

14 PIN CERAMIC DUAL-IN-LINE MIL-STD-1835 DESIGNATOR, CDIP2-T14, LEAD FINISH C



14 PIN CERAMIC FLATPACK MIL-STD-1835 DESIGNATOR, CDFP3-F14 LEAD FINISH C

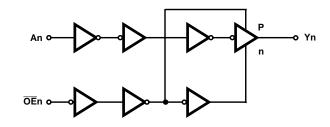
TOP VIEW



Ordering Information

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9671501VCC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead SBDIP
5962F9671501VXC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead Ceramic Flatpack
ACTS125D/Sample	25°C	Sample	14 Lead SBDIP
ACTS125K/Sample	25°C	Sample 14 Lead Ceramic Flatpac	
ACTS125HMSR	25°C	Die	Die

Functional Diagram



TRUTH TABLE

INP	OUTPUT	
An	OEn	Yn
L	L	L
Н	L	Н
Х	Н	Z

NOTE: L = Low, H = High, X = Don't Care, Z = High Impedance

ACTS125MS

Die Characteristics

DIE DIMENSIONS:

88 x 88 (mils) 2.24 x 2.24 (mm)

METALLIZATION:

Type: AISi

Metal 1 Thickness: $7.125k\mathring{A} \pm 1.125k\mathring{A}$ Metal 2 Thickness: $9k\mathring{A} \pm 1k\mathring{A}$

GLASSIVATION:

Type: SiO₂

Thickness: 8kÅ ± 1kÅ

WORST CASE CURRENT DENSITY:

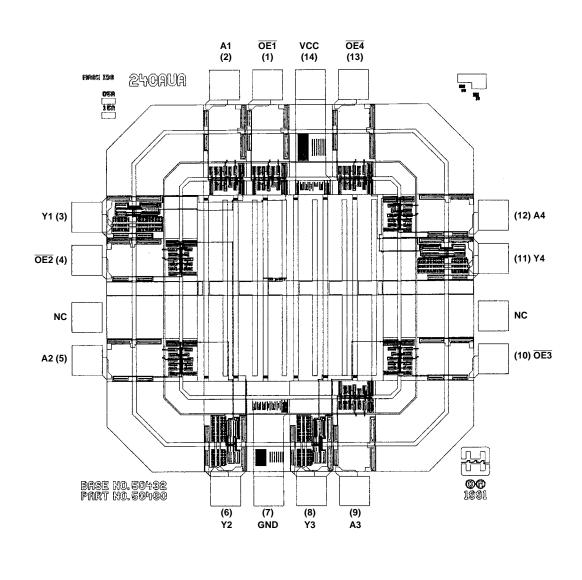
 $<2.0 \times 10^5 \text{ A/cm}^2$

BOND PAD SIZE:

> 4.3 x 4.3 (mils) > 110 x 110 (μm)

Metallization Mask Layout

ACTS125MS



ACTS125MS

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